

Spin Transport in Magnetic 2D Materials and Heterostructures

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2D VAN DER WAALS SPIN SYSTEMS SPICE || August 4th 2020



Outline

- I. Introduction to Magnetic 2D Materials
- II. Spin (Magnon) Transport in Insulating MnPS₃ Flakes
- III. Spin (Electron) Transport in Metallic FeTaS₂ Flakes
 - > Spin scattering mechanisms in $FeTaS_2$
 - ➢ Spin transport in FeTaS₂/SC junctions

IV. Summary

Introduction to Magnetic 2D Materials



Nobel Prize in physics (2010)

Making Graphene Magnetic

Doping of magnetic impurity



Magnetic proximity effect



Yazyev and Helm, PRB (2007) Han, et al, Nature Nanotech (2014)

FM insulator: YIG (Y₃Fe₅O₁₈), EuO

AFM insulator: BiFeO₃

Haugen, et al, PRB (2008) Qiao, et al, PRL (2010) Wei, et al, Nature Materials (2016) Wang, et al, PRL (2015)

Making graphene magnetic

Doping of magnetic impurity



Nair, et al, Nature Physis (2010)

Making graphene magnetic



Introduction to Magnetic 2D Materials



Introduction to Magnetic 2D Materials

Doping of magnetic impurity

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Extrinsic ferromagnetism

How about intrinsic 2D ferromagnetism?



Bulk Cr₂Ge₂Te₆



Layered structure

V. Carteaux, et al, J. Phys.: Condens. Matter 7, 69 (1995);

H. Ji, et al, J. Appl. Phys. (2013)

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Bulk Cr₂Ge₂Te₆



Layered structure

V. Carteaux, et al, J. Phys.: Condens. Matter 7, 69 (1995);

¹⁰ H. Ji, et al, J. Appl. Phys. (2013)

Flux method



XRD



Ferromagnetic

Semiconducting



X. Zhang, Y. Zhao, Q. Song, S. Jia, J. Shi, and <u>W. Han*</u>, **Jpn. J. Appl. Phys. 55, 033001 (2016)**

Ferromagnetic 2D flakes

2D flakes: Mechanical exfoliation



W. Xing, Y. Chen, P. Odenthal, X. Zhang, W. Yuan, T. Su, Q. Song, T. Wang, S. Jia, X. C. Xie, Y. Li, and <u>W. Han*</u>, **2D Materials**, **4**, **024009** (2017)

Cr₂Ge₂Te₆



Crl₃

Gong, et al, Nature (2017); Huang, et al, Nature (2017)

Introduction to Magnetic 2D Materials

Chalcogenides	$Cr_2Ge_2Te_6, Cr_2Si_2Te_6, Fe_3GeTe_2, VSe_2^*, MnSe_x^*$	$\begin{array}{l} Fe_{2}P_{2}S_{6}, Fe_{2}P_{2}Se_{6}, Mn_{2}P_{2}S_{6}, Mn_{2}P_{2}Se_{6}, Ni_{2}P_{2}S_{6}, Ni_{2}P_{2}Se_{6}, CuCrP_{2}Se_{6}^{*},\\ AgVP_{2}S_{6}, AgCrP_{2}S_{6}, CrSe_{2}, CrTe_{3}, Ni_{3}Cr_{2}P_{2}S_{9}, MnBi_{2}Te_{4}^{*}, MnBi_{2}Se_{4}^{*} \end{array}$		CuCrP ₂ S ₆
Halides	CrI ₃ *, CrBr ₃ , GdI ₂	CrCl ₃ , FeCl ₂ , FeBr ₂ , FeI ₂ , MnBr ₂ , CoCl ₂ , CoBr ₂ , NiCl ₂ , VCl ₂ , VBr ₂ , VI ₂ , FeCl ₃ , FeBr ₃ , CrOCl, CrOBr, CrSBr, MnCl ₂ [*] , VCl ₃ [*] , VBr ₃ [*]	CuCl ₂ , CuBr ₂ , NiBr ₂ , NiI ₂ , CoI ₂ , MnI ₂	
			α-RuCl ₃	
Others	VS ₂ , InP ₃ , GaSe, GaS	$MnX_3 (X = F, Cl, Br, I), FeX_2 (X = Cl, Br, I),$ MnSSe, TiCl ₃ , VCl ₃	SnO, GeS, GeSe, SnS, SnSe, GaTeCl, CrN, CrB ₂	



Burch, et al., Nature (2018); Gong, et al., Science (2019)

This Talk: Spin Transport in 2D Magnets



Magnon for information computing



Chumak, et al., Nature Physics (2015)

Nonlocal spin transport and magnon transistor



Cornelissen, et al., PRL (2018)

MnPS₃ properties

Crystal and spin structures



Device fabrication





Nonlocal Magnon transport

Injector: Thermal spin injection

Detector: Inverse spin Hall effect



Thermal magnons



Control device fabricated on SiO₂/Si substrates



The absence of spin signal on the control device rules out the possibility of signals from the SiO_2/Si substrate.

Magnon signal – Exponential decay



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Magnon signal – Exponential decay



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Magnon signal – Exponential decay



Magnon signal – Exponential decay



The Criteria (exponential vs. $1/d^2$): Shan, et al., PRB (2017)

Absence of magnon signals in thin MnPS₃



Magnon relaxation length in 2D MnPS₃



W. Xing, L. Qiu, X. Wang, Y. Yao, Y. Ma, R. Cai, S. Jia, X. C. Xie, and <u>W. Han*</u>, **Physical Review X 9, 011026 (2019)**



Wenyu Xing

This Talk: Spin Transport in 2D Magnets



Electron spin scattering in metallic FeTaS₂ flakes

Anomalous Hall effect Mechanisms in FM



Nagaosa, et.al., Rev. Mod. Phys. (2010)

Electron spin Transport in Metallic FeTaS₂ Flakes

Layered FeTaS₂



Fe_{0.29}TaS₂



Anomalous Hall resistance in 2D Fe_{0.29}TaS₂

Device fabrication and AHE measurement



Anomalous Hall resistance in 2D Fe_{0.29}TaS₂

Device fabrication and AHE measurement



 $T_C \sim 80$ K, similar to bulk

Anomalous Hall resistance in 2D Fe_{0.29}TaS₂

Thickness dependence of B_c of $Fe_{0.29}TaS_2$



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Anomalous Hall mechanism in FM

Scaling relationship



Nagaosa, et.al., Rev. Mod. Phys. (2010); Onoda, et.al., Phys. Rev. B. (2008)

Scaling relationship

$$\sigma_{AHE}^* = \sigma_{AHE}/M = \alpha_0 \sigma_{xx} + \beta_0^*$$



Thickness dependent AHE Mechanisms

$$\sigma_{AHE}^* = \alpha_0 \sigma_{xx} + \beta_0^*$$



AHE Mechanisms vs. Channel conductivity



AHE Mechanisms vs. Channel conductivity



R. Cai, W. Xing, H. Zhou, B. Li, Y. Chen, Y. Yao, Y. Ma, X. C. Xie, S. Jia, and <u>W. Han*</u>, **Physical Review B**, 100, 054430 (2019)

Summary: Spin Transport in 2D Magnets



Outlook: Spin Transport in 2D Magnets



Acknowledgement

Collaborators



Shuang Jia



Qing-Feng Sun



Igor Zutic



Xin-Cheng Xie

Students



Wenyu Xing



Ranran Cai



Funding

NSF-China National Basic R&D

Acknowledgement-audience





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